L Number	Hits	Search Text	DB	Time stamp
1	50	corning adj glass adj "7059"	USPAT	2003/06/12 11:18
2	1	us-5622814-\$.did. and (al aluminum)	USPAT	2003/06/12 11:38
3	9110	active adj matrix	USPAT	2003/06/12 11:40
4	39	1	USPAT	2003/06/12 11:47
5	6356		USPAT;	2003/06/12 11:40
	0000	device mems!	US-PGPUB;	2000, 00, 22 22000
	,		EPO; JPO;	İ
			DERWENT	
6	27721	active adj matrix	USPAT;	2003/06/12 11:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
7	10	(microelectromechanical adj system adj	USPAT;	2003/06/12 11:40
		device mems!) with (active adj matrix)	US-PGPUB;	
			EPO; JPO;	
1			DERWENT	
8	2		USPAT	2003/06/12 11:47
1_		430/\$.ccls.		0000/06/10 11 40
9	4100	(semiconductor) with repeat\$3	USPAT	2003/06/12 11:48
10	369	((semiconductor) with repeat\$3) and	USPAT	2003/06/12 11:48
	0011	430/\$.ccls.	I II CDAM	2003/06/12 11:50
11	2011	(semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:50
12	225	method process)	USPAT	2003/06/12 11:50
12	225	((semiconductor) with repeat\$3 with (step method process)) and 430/\$.ccls.	USFAI	2003/00/12 11:30
14	225	(((semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:51
1 -1	223	method process)) and 430/\$.ccls.) and	JULAI	2005,00,12 11.51
		430/\$.ccls.		
15	22	((semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:51
		method process) with (known typical\$3		
		conventional\$3)) and 430/\$.ccls.		
16	2909	(backside back-side back adj side) near2	USPAT;	2003/06/12 12:26
		(expos\$4 irradiat\$5)	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
17	1		USPAT;	2003/06/12 11:55
		method process)) same ((backside back-side	US-PGPUB;	
		back adj side) near2 (expos\$4 irradiat\$5)	EPO; JPO;	
		[]	DERWENT	0000/06/10 11 55
18	15		USPAT;	2003/06/12 11:55
		method process)) and ((backside back-side	US-PGPUB; EPO; JPO;	
		back adj side) near2 (expos\$4 irradiat\$5)	DERWENT	
19	0	(semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:57
1 1 9		method process) with (known typical\$3	OSTAT	2003/00/12 11.37
		conventional\$3) with (many multiple) with		
		layer		
20	3		USPAT	2003/06/12 11:57
		method process) with (known typical\$3		
		conventional\$3) with (many multiple)	1	
13	130		USPAT	2003/06/12 11:59
		method process) with (known typical\$3		
		conventional\$3)		
21	85		USPAT	2003/06/12 12:10
]		method process) with (known typical\$3		
		conventional\$3)		
22	2		USPAT	2003/06/12 12:11
		method process) with (required) with		
1 22		(multiple near2 layer)	HCDAM	2002/06/10 10:10
23	0	(electrodes) with repeat\$3 with (steps!	USPAT	2003/06/12 12:12
		method process) with (required) with (multiple near2 layer)		
24	1789		USPAT	2003/06/12 12:13
	1,09	method process)	1 221.21	2003/00/12 12:13
25	58		USPAT	2003/06/12 12:18
	33	method process) with (known conventional\$2	332731	2003, 00, 12 12.10
		typical\$2)	1	
26	323		USPAT	2003/06/12 12:18
		method process) with (known conventional\$2		
		typical\$2)		
	L	1	1	·

27	81	with repeat\$3 with (steps! method process)	USPAT	2003/06/12 12:19
28	11941	<pre>with (known conventional\$2 typical\$2)) (back) near2 (expos\$4 irradiat\$5)</pre>	USPAT; US-PGPUB;	2003/06/12 12:26
29	10292	((back) near2 (expos\$4 irradiat\$5)) not	EPO; JPO; DERWENT USPAT;	2003/06/12 12:27
		((backside back-side back adj side) near2 (expos\$4 irradiat\$5))	US-PGPUB; EPO; JPO; DERWENT	
30	151	(((back) near2 (expos\$4 irradiat\$5)) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))) same repeat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:28
31	63	<pre>(((back) near2 (expos\$4 irradiat\$5)) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))) same (repeat\$3 with (steps method process))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:32
32	2		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 12:32
_	26	MILES-MARKin. MILES-MARK-Win. MILES-M-Win.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/11 16:34
-	2907	(backside back-side back adj side) near2 (expos\$4 irradiat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:52
-	398591	resist photoresist photo-resist	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:38
_	311632	<pre>photosensitive photo-sensitive (sensitive near (photo light energy radiation))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:39
-	357428	uv ultraviolet ultra-violet ultra adj violet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:40
_	32060	<pre>((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:46
_	24	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative) same (uv ultraviolet ultra-violet ultra adj violet)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:32
_	2	("5674757").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:34
-	6323	microelectromechanical adj system adj device mems!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:40
_	34	<pre>(microelectromechanical adj system adj device mems!) and ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:04

-	7	(microelectromechanical adj system adj	USPAT;	2003/06/11 17:44
		device mems!) and ((backside back-side	US-PGPUB;	
		back adj side) near2 (expos\$4 irradiat\$5))	EPO; JPO;	
		and (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive	DERWENT	
		near (photo light energy radiation))))		
		with negative)		
_	28	(ni nickel al aluminum) same ((backside	USPAT;	2003/06/11 17:52
		back-side back adj side) near2 (expos\$4	US-PGPUB;	
		irradiat\$5)) same ((resist photoresist	EPO; JPO;	
		photo-resist) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo		
		light energy radiation))) (((resist photoresist photo-resist) (photosensitive		
		photo-sensitive (sensitive near (photo		
		light energy radiation)))) with negative))		
-	177		USPAT;	2003/06/11 17:57
		(expos\$4 irradiat\$5)) same (groove strip	US-PGPUB;	
		stripe transvers\$4 longitudinal\$4)	EPO; JPO;	
			DERWENT	
-	4	(((backside back-side back adj side) near2	USPAT;	2003/06/11 17:55
		(expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same	US-PGPUB; EPO; JPO;	
		(((resist photoresist photo-resist)	DERWENT	
		(photosensitive photo-sensitive (sensitive		
		near (photo light energy radiation))))		
		with negative)		
-	17	, , , , , , , , , , , , , , , , , , ,	USPAT;	2003/06/11 17:55
		near2 (expos\$4 irradiat\$5)) same (groove	US-PGPUB;	
		strip stripe transvers\$4 longitudinal\$4)) same ((resist photoresist photo-resist)	EPO; JPO; DERWENT	
		(photosensitive photo-sensitive (sensitive	DERWENT	
		near (photo light energy radiation)))))		:
		not ((((backside back-side back adj side)		
		near2 (expos\$4 irradiat\$5)) same (groove		
		strip stripe transvers\$4 longitudinal\$4))		
		same (((resist photoresist photo-resist)		
		<pre>(photosensitive photo-sensitive (sensitive near (photo light energy radiation))))</pre>		
		with negative))		
-	50	((backside back-side back adj side) near2	USPAT;	2003/06/11 17:58
		(expos\$4 irradiat\$5)) same (transvers\$4	US-PGPUB;	
		longitudinal\$4)	EPO; JPO;	
			DERWENT	0002/06/11 10:01
-	6	(((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (transvers\$4	USPAT;	2003/06/11 18:01
		longitudinal\$4)) and ((resist photoresist	US-PGPUB; EPO; JPO;	
		photo-resist) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo		
1		light energy radiation))) 430/\$.CCLS.)		
-	2		USPAT;	2003/06/11 18:01
		(expos\$4 irradiat\$5)) SAME	US-PGPUB;	
1		<pre>(microelectromechanical adj system adj device mems!)</pre>	EPO; JPO; DERWENT	
_	1003	((backside back-side back adj side) near2	USPAT;	2003/06/11 18:07
	1000	(expos\$4 irradiat\$5)) with ((resist	US-PGPUB;	2000,00,11 10.07
		photoresist photo-resist) (photosensitive	EPO; JPO;	
		photo-sensitive (sensitive near (photo	DERWENT	
Ì		light energy radiation))) (uv ultraviolet		
		ultra-violet ultra adj violet) laser mask		
_	584	<pre>photomask light) ((backside back-side back adj side) near2</pre>	HCDATT.	2003/06/11 18:11
_	504	((packside back-side back ad) side) hearz (expos\$4 irradiat\$5)) with ((resist	USPAT; US-PGPUB;	2003/06/11 18:11
		photoresist photo-resist) (photosensitive	EPO; JPO;	
		photo-sensitive (sensitive near (photo	DERWENT	
		light energy radiation))) (uv ultraviolet	,	
		ultra-violet ultra adj violet) (((resist		
		photoresist photo-resist) (photosensitive		
		<pre>photo-sensitive (sensitive near (photo light energy radiation)))) with negative)</pre>		
		mask photomask)		
L	L		L	1

- 410 ((backside back-side back adj side)	
(expos\$4 irradiat\$5)) with ((resist	US-PGPUB
photoresist photo-resist) (photosens:	
photo-sensitive (sensitive near (photo-	
light energy radiation))) (uv ultrav	
ultra-violet ultra adj violet) (((res	I I I
photoresist photo-resist) (photosens:	itive
photo-sensitive (sensitive near (photo-	to
light energy radiation)))) with negat	tive)
mask photomask)	
- 58 (((backside back-side back adj side)	near2 USPAT; 2003/06/11 18:59
(expos\$4 irradiat\$5)) with ((resist	US-PGPUB
photoresist photo-resist) (photosens:	itive
photo-sensitive (sensitive near (photo-	to
light energy radiation))) (uv ultrav	iolet
ultra-violet ultra adj violet) mask	
photomask)) same negative	
- 1 us-6304309-\$.did. and (orthogonal\$3	USPAT; 2003/06/11 19:01
transvers\$5)	US-PGPUB
- 324 ((backside back-side back adj side) r	near2 USPAT; 2003/06/11 19:01
(expos\$4 irradiat\$5)) and (orthogonal	
transvers\$5)	EPO; JPO;
	DERWENT
- 18 ((backside back-side back adj side) r	
(expos\$4 irradiat\$5)) same (orthogona	
transvers\$5)	EPO; JPO;
	DERWENT
- 23 (((backside back-side back adj side)	
(expos\$4 irradiat\$5)) same ((resist	US-PGPUB;
photoresist photo-resist) (photosens	1 ' 1
photo-sensitive (sensitive near (phot	
light energy radiation))))) and (layer	
same (orthogonal\$3 transvers\$5))	